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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SiBar™ **Thyristor Surge Protectors**

PRODUCT: TVB170SC-L

DOCUMENT: SCD 25897

PCN: F01905 **REV LETTER: B**

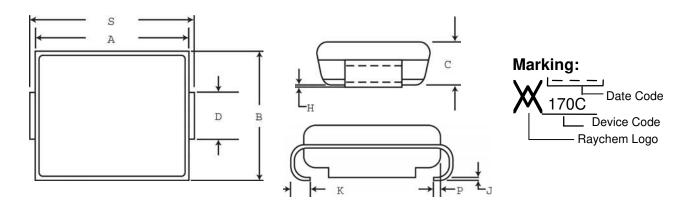
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Specification Status: RELEASED

Raychem Circuit Protection Products

PHYSICAL DESCRIPTION



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	MIN	MAX												
mm:	4.06	4.57	3.30	3.81	1.90	2.41	1.96	2.11	0.051	0.152	0.15	0.30	0.76	1.27
in*:	(0.160)	(0.180)	(0.130)	(0.150)	(0.075)	(0.095)	(0.077)	(0.083)	(0.002)	(0.006)	(0.006)	(0.012)	(0.030)	(0.050)

REF MIN MAX mm: 0.51 5.21 5.59 in*: (0.020) (0.205) (0.220)

Other Physical Characteristics

SMB (Surface Mount, JEDEC DO-214AA Package) Form Factor:

Lead Material: Matte Tin Finish

Epoxy, meets UL94 V-0 requirements **Encapsulation Material:** Solderability: per MIL-STD-750, Method 2026 Solder Heat Withstand: per MIL-STD-750, Method 2031 per MIL-STD-750, Method 1022 Solvent Resistance: Mechanical Shock: per MIL-STD-750, Method 2016 Vibration: per MIL-STD-750, Method 2056

Tape and Reel packaging per EIA 481-1

Agency Recognition:

Precedence: This specification takes precedence over documents referenced herein.

CAUTION: Operation beyond the rated voltage or current may result in rupture, electrical arcing or flame.

Materials Information

RoHS Compliant ELV Compliant

Directive 2002/95/EC Compliant

Directive 2000/53/EC Compliant

^{*}Rounded off approximation

^{**} D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P



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DEVICE RATINGS @ 25º C (Both Polarities)

	Parameter	Symbol	Value	Units
Repetitive Off-State Vo	repetitive Off-State Voltage, Maximum at ID = 5 µA Ion-Repetitive Peak repulse Current rouble exponential Vaveform Notes 1 and 2) Telcordia GR-1089 CORE 10x1000 µ TIA-968 lightning Type A Metallic 10/560 µ TIA-968 lightning Type A Longit. 10/160 µ Telcordia GR-1089 Intrabuilding 2/10 µ IEC61000-4-5 (Voc 1.2/50us) 8/20 µ ITU-T K.20/K.21 (Voc 10/700us) 5/310 µ		170	٧
Non-Repetitive Peak	Telcordia GR-1089 CORE 10x1000 μs	IPP₁	100	Α
Impulse Current	TIA-968 lightning Type A Metallic 10/560 μs	IPP ₂	150	Α
Double exponential	TIA-968 lightning Type A Longit. 10/160 µs	IPP ₃	200	Α
Waveform	Telcordia GR-1089 Intrabuilding 2/10 μs	IPP ₄	500	Α
(Notes 1 and 2)	IEC61000-4-5 (Voc 1.2/50us) 8/20 μs	IPP ₅	400	Α
	ITU-T K.20/K.21 (Voc 10/700us) 5/310 μs	IPP ₆	150	Α
	TIA-968 lightning Type B (Voc 9/720us) 5/320 μs	IPP ₇	150	Α
Critical Rate of Rise of				
Power Pulse Amplifier,	$C = 30\mu F$, $V max = 600 V$	di/dt	500	A/μs
Maximum 2x10 µsec w	aveform, V _{OC} =2.5kV, I _{SC} =500A peak	di/dt	330	A/µs

DEVICE THERMAL RATINGS

Storage Temperature Range	TSTG	-55 to 150	ōC
Operating Temperature Range	TA	-40 to 125	ōC
Blocking or conducting state			
Overload Junction Temperature	TJ	+150	ōC
Maximum; Conducting state only			
Maximum Lead Temperature for Soldering Purpose; for 10 seconds	TL	+260	ōC

ELECTRICAL CHARACTERISTICS Both polarities (T₁@ 25°C unless otherwise noted)

Characteristics		Symbol	Min	Тур	Max	Units
()	25ºC)	VBO		230	265	V
$(dv/dt = 0.4kV/\mu sec, I_{SC}=900mA, V_{DC}=500V (both polarite)$	ues))					
Breakover Voltage Temperature Coefficient		dVBO/dTJ		0.1		%/ºC
Off-State Current (VD1=	= 50V)	ID1			2.0	μΑ
(VD2=	:VDM)	ID2=IDM			5.0	μΑ
On-State Voltage (I	T=1A)	VT			4.0	V
(PW ≤ 300 μsec, Duty Cycle ≤ 2% (Note 2))						
Breakover Current		IBO			800	mA
Holding Current (Note 2)		ΙΗ	150			mA
Peak Onstage Surge Current		ITSM	60			Α
(Measured @ 60Hz, 1 cycle, 600V)						
Critical Rate of Rise of Off-State Voltage		dv/dt	5000			V/µs
(Linear waveform, $V_D = 0.8 \text{ X Rated } V_{BO}, T_{J} = +25^{\circ}C$)						
Capacitance (f=1.0 Mhz, 50Vdc bias, 1 V	Vrms)	C1		60		pF
(f=1.0 Mhz, 2Vdc bias, 1)	Vrms)	C2		125		pF

Note 1. Allow cooling before test second polarity

Note 2. Measured under pulse conditions to reduce heating

VOLTAGE-CURRENT CHARACTERISTIC

